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Raghavendra Rao Juluri, Peter Gaiduk, John Lundsgaard Hansen, Arne Nylandsted Larsen, Brian Julsgaard

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Raghavendra Rao Juluri[1]

Peter Gaiduk[2, 3]

John Lundsgaard Hansen[1, 2]

Arne Nylandsted Larsen[1, 2]

Brian Julsgaard[1, 2]

1Interdisciplinary Nanoscience Center (iNano), Aarhus University, Gustav Wieds Vej 14, DK-8000 Aarhus C, Denmark.

2Department of Physics and Astronomy, Aarhus University, Ny Munkegade 120, DK-8000 Aarhus C, Denmark.

3Department of Physical Electronics and Nanotechnologies, Belarussian State University, Praspyekt Nyezalyezhnastsi 4, 220030 Minsk, Belarus.